

**In the Claims:**

**Claims 1-3 (cancelled)**

**Claim 4 (currently amended):** A method for depositing micro-lenses on a semiconductive circuit comprising the steps of:

applying a first coat of micro-lens suitable material to a the surface of a the semiconductive circuit;

imparting a first lens formation pattern onto the first coat of micro-lens suitable material, wherein the first lens formation pattern includes a boundary for each of a first plurality of micro-lenses to be formed, and wherein the first lens formation pattern further includes a first setback from the boundary for each of the first plurality of micro-lenses to be formed;

removing unwanted portions of the first coat of micro-lens suitable material;

forming a the first plurality of micro-lenses from the remaining first coat of micro-lens suitable material;

applying a second coat of micro-lens suitable material to the semiconductive circuit;

imparting a second lens formation pattern to the second coat of micro-lens suitable material, wherein the second lens formation pattern includes a boundary for each of a second plurality of micro-lenses to be formed, and wherein the second lens formation pattern further includes a second setback from the boundary for each of the second plurality of micro-lenses to be formed;

removing unwanted portions of the second coat of micro-lens suitable material; and

forming a the second plurality of micro-lenses from the remaining second coat of micro-

lens suitable material.

**Claim 5 (original):** The method of Claim 4 wherein the first and second lens formation patterns are alternate counterparts of each other.

**Claim 6 (original):** The method of Claim 5 wherein the first and second lens formation patterns comprise rectangular regions in a checkerboard pattern.

**Claim 7 (cancelled)**

**Claim 8 (original):** The method of Claim 4 wherein the step of forming the first and second plurality of micro-lenses comprise the steps of:

raising the temperature of the micro-lens suitable material in order to relieve the surface tension thereof;

allowing the micro-lens suitable material to reflow in order to achieve a desired lens focal length; and

reducing the temperature of the micro-lens suitable material in order to preserve the achieved lens focal length.

**Claim 9 (currently amended):** The method of Claim ~~4~~ 4 wherein the step of applying the first and second coats of micro-lens suitable material comprise the step of spin coating a micro-lens suitable material onto the semiconductive circuit.

**Claim 10 (currently amended):** The method of Claim ~~1~~ 4 wherein the step of imparting the a first lens formation pattern onto the first coat of micro-lens suitable material comprises the steps of:

placing a first formation mask comprising the first lens formation pattern proximate to the first coat of micro-lens suitable material;

aligning the first formation mask relative to the semiconductive circuit; and

illuminating the first formation mask with radiation.

**Claims 11-32 (canceled).**

**Claim 33 (new):** The method of Claim 4 wherein the first setback from the boundary is less than a setback for a single pass micro-lens formation method.

**Claim 34 (new):** The method of Claim 4 wherein the second setback from the boundary is less than a setback for a single pass micro-lens formation method.